



HY14E10

Datasheet

Digital Pressure Sensor Platform

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1. 特點

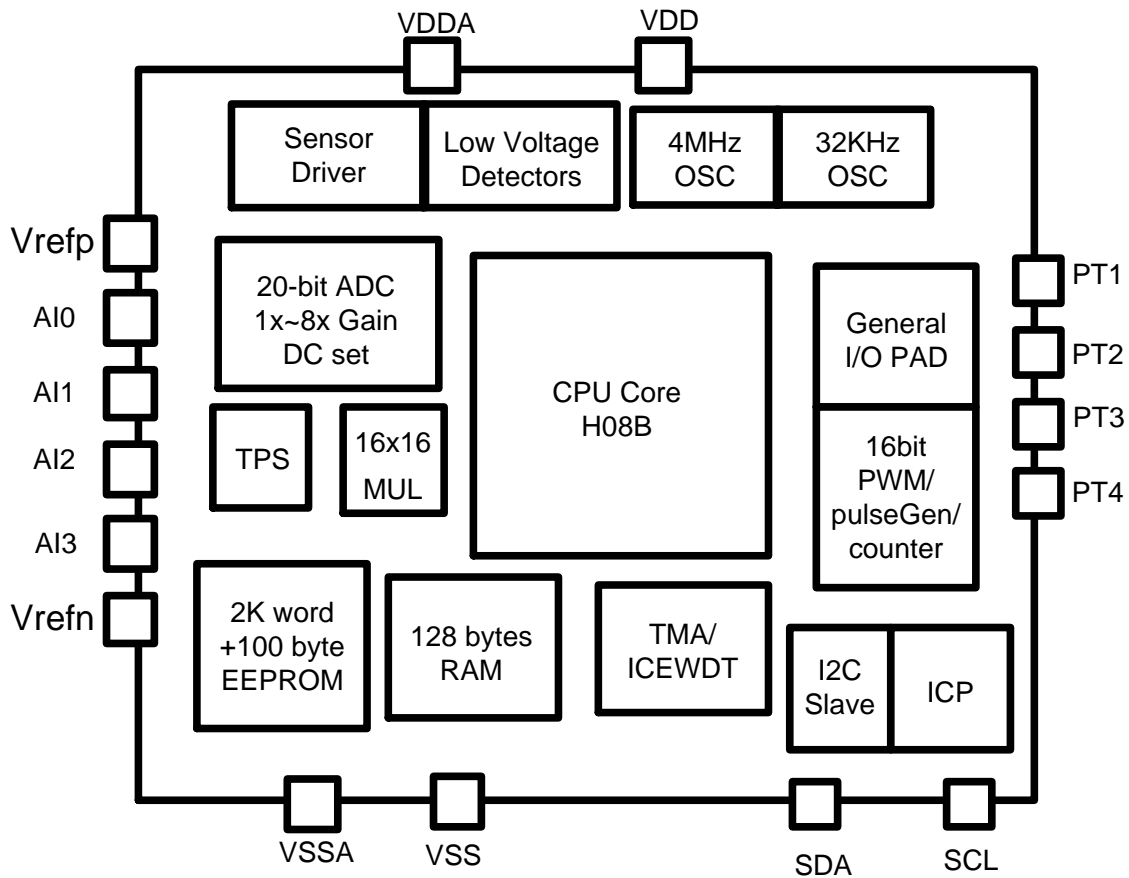
- 用於整合式壓阻壓力傳感器
 - 內建一個 20 位元 ADC，用於電壓和溫度測量
 - 內建一個 PGA 輸入信號放大
- 較寬的工作電壓範圍: 2.0V ~ 5.5V
- 內建 2K words EEPROM
 - 支援線上燒錄
 - 100,000 燒錄次數
- 128 bytes SRAM
- 16bit x 16bit 硬體乘法器
- I²C 從機通訊界面
- 4 個通用 I/O 埠(PT0/PT1 支援輸入中斷功能)
- 16-bit PWM
- 2 線式 JTAG 開發介面(與 I²C 共用)
- 可程式感測器驅動電壓
- 只有 VDD 外部電容是必需的
- 內建 VDDA LDO(選擇性啟動)
- 兩組類比多工輸入

功能列表

Model No.	VDD	System Clock	Program Memory (word)	SRAM (byte)	ADC ENOB (bit x ch)	Sample Rate (sps)	TPS	I/O	Timer (bit x ch)	PWM (bit x ch)	Serial I/F	Package
HY14E10	2.0V~5.5V	32KHz~4MHz	2K	128	19bit x 4	60~7.8K	yes	4	8-bit x 1 16-bit x 1	8-bit x 1 16-bit x 1	I ² C Slave	QFN16 SSOP16

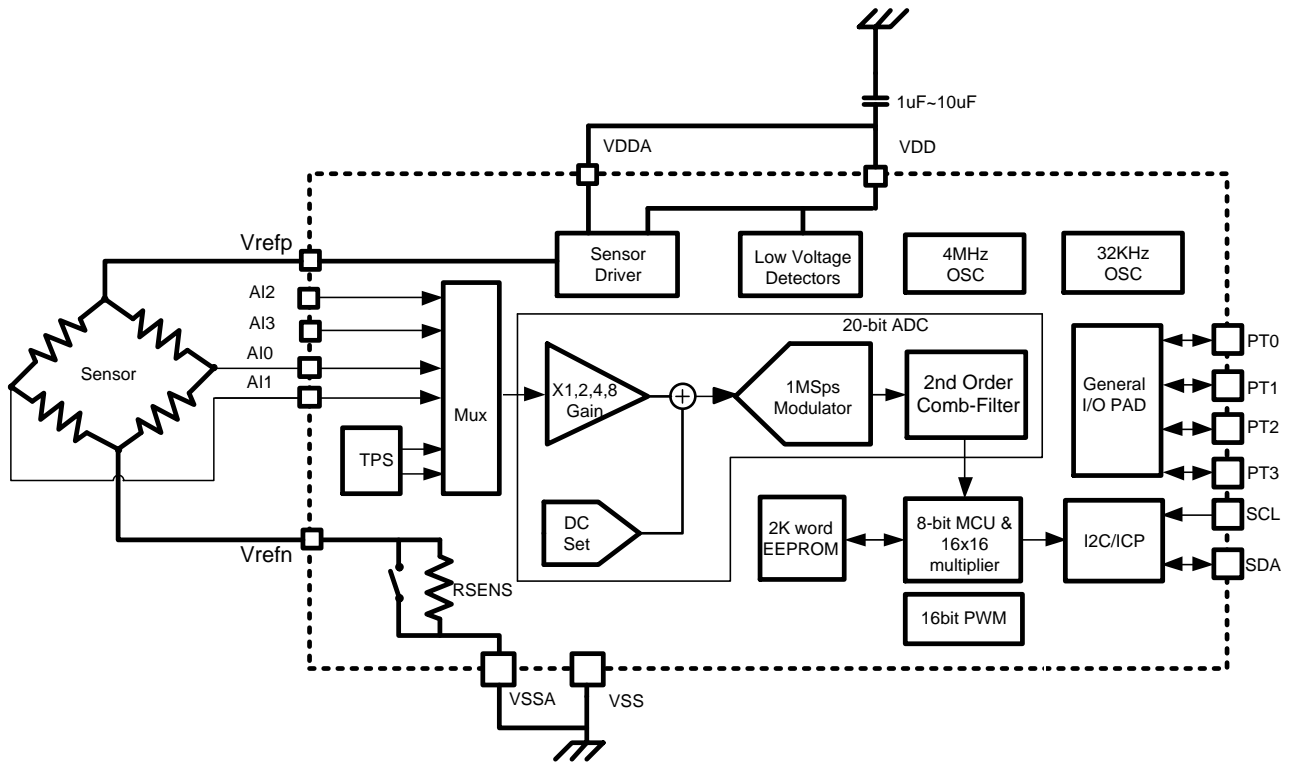
2. 功能概述

2.1. 內部方塊圖



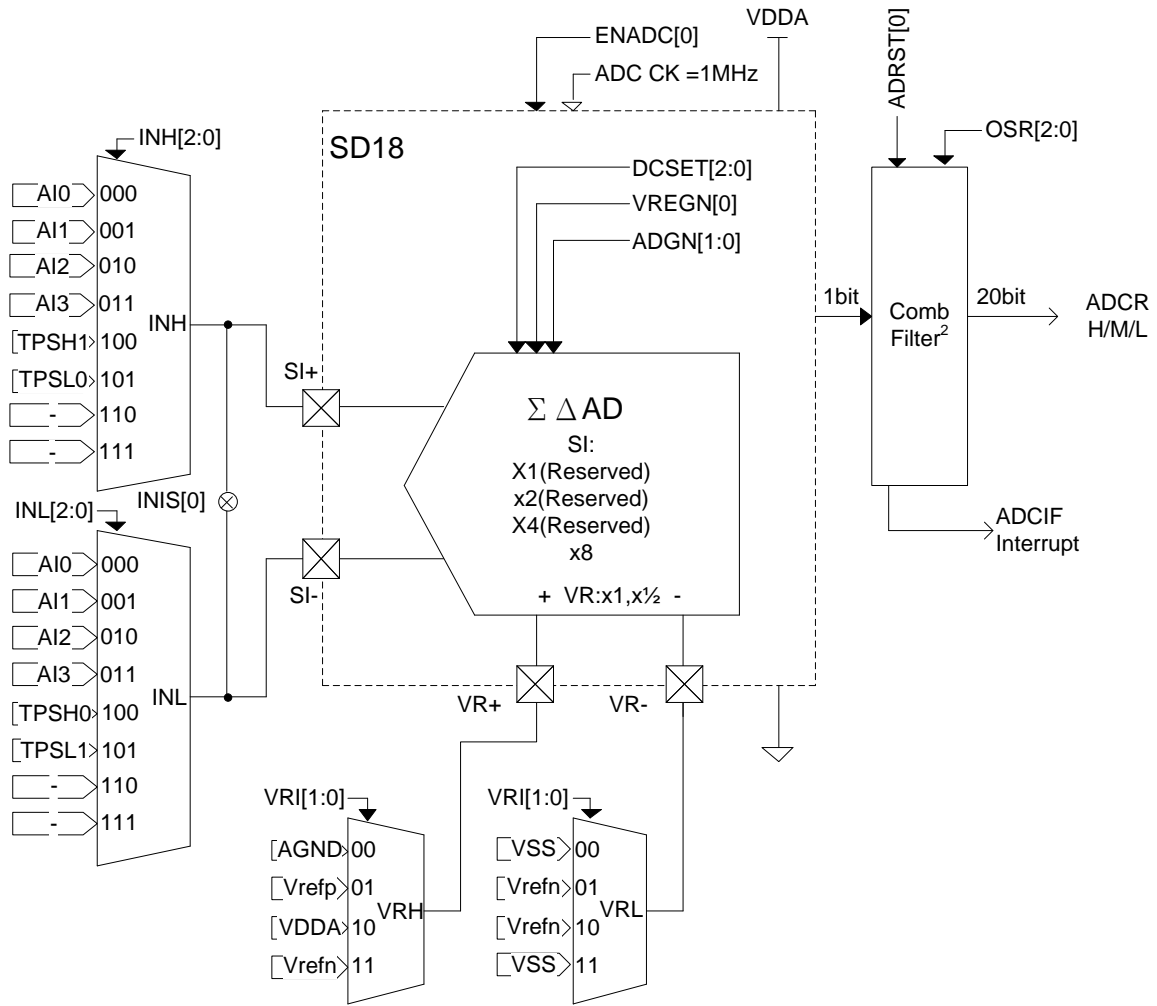
Note : 在電壓放大倍率 x1/x2/x4 為 Reserved , 建議使用 8 倍放大倍率。

2.2. 應用電路



Note : 在電壓放大倍率 x1/x2/x4 為 Reserved , 建議使用 8 倍放大倍率。

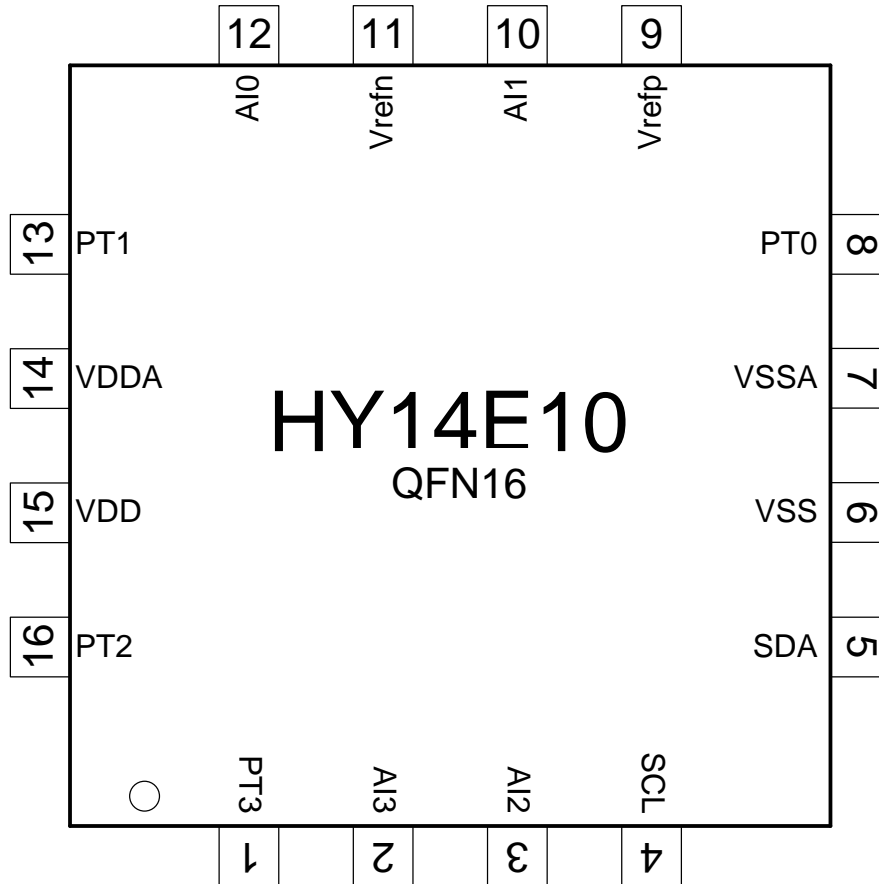
2.3. SD18 Network



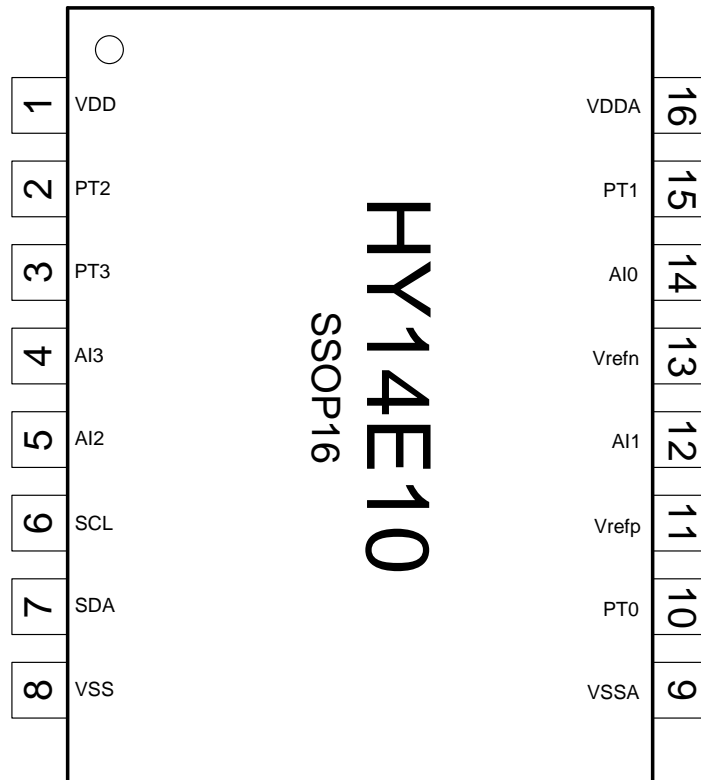
Note : 在電壓放大倍率 x1/x2/x4 為 Reserved，建議使用 8 倍放大倍率。

3. 包裝與引腳定義

3.1. QFN16(N016)引腳圖



3.2. SSOP16(E016)引腳圖



3.3. 引腳定義說明

N016	E016	Pin	Characteristic		Description
		Name	I/O	Type	
11	13	Vrefn	O	A	Sense Ground.

					Used to ground resistive bridge sensor.
12	14	AI0	I	A	Sensing Input 0. Used for analog input to ADC multiplexer
13	15	PT1	I/O	S	Digital Input/Output Port 1 Used as general digital input or output pad. It has level change interrupt
14	16	VDDA	I	P	Analog Power Supply. A 2.0V ~ 5.5V voltage input. (Short with VDD by wire bonding or LDO output option)
15	1	VDD	I	P	Power Supply. A 2.0V ~ 5.5V voltage input. Connect a 1uF capacitor to VSS.
16	2	PT2	I/O	S	Digital Input/Output Port 2 Used as general digital input or output pad. It has level change interrupt
1	3	PT3	I/O	S	Digital Input/Output Port 3 Used as general digital input or output pad
2	4	AI3	I	A	Sensing Input 3. Used for analog input to ADC multiplexer
3	5	AI2	I	A	Sensing Input 2. Used for analog input to ADC multiplexer
4	6	SCL	I	C	I2C Serial Clock Input. Slave I2C communication clock line
5	7	SDA	I/O	D	I2C Serial Data Input/Output Slave I2C communication data line. Open-drain output. Use with an external pull-up resistor
6	8	VSS	I	P	Device Ground.
7	9	VSSA	I	P	Device Analog Ground.
8	10	PT0	I/O	S	Digital Input/Output Port 0 Used as general digital input or output pad
9	11	Vrefp	O	A	Power Supply. Used to power resistive bridge sensor.
10	12	AI1	I	A	Sensing Input 1. Used for analog input to ADC multiplexer

"I/O" Input/Output, "I" Input, "O" Output, "D" Digital Open-Drain, "S" Schmitt Trigger, "C" CMOS, "P" Power, "A" Analog

4. 暫存器列表

“-”no use, “*”read/write, “w”write, “r”read, “r0”only read 0, “r1”only read 1, “w0”only write 0, “w1”only write 1												
“\$”for event status, “.”unimplemented bit, “x”unknown, “u”unchanged, “d”depends on condition												
Address	File Name	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	A-RESET	R/W	
00H	INDF0	Contents of FSR0 to address data memory value of FSR0 not changed									N/A	*****
0FH	FSR0H								X*	
10H	FSR0L	Indirect Data Memory Address Pointer 0 Low Byte, FSR0[7:0]									xxxx xxxx	*****
16H	TOSH	-	-	-	-	-	TOS[10]	TOS[9]	TOS[8] 0000*	
17H	TOSL	Top-of-Stack Low Byte (TOS<7:0>)									0000 0000	*****
18H	STKPTR	STKFL	STKUN	STKOV	-	-	STKPR[2:0]			000. 000	r,rw0,rw0,-,r,r,r	
1AH	PCLATH	-	-	-	-	-	PC[10]	PC[9]	PC[8] 0000*	
1BH	PCLATL	PC Low Byte for PC<7:0>									0000 0000	*****
1DH	TBLPTRH	TBLW+	TBLW	TBLR+	TBLR	TBLPTR[11]	TBLPTR[10]	TBLPTR[9]	TBLPTR[8] 0000*	
1EH	TBLPTRL	Program Memory Table Pointer Low Byte (TBLPTR<7:0>)									0000 0000	*****
20H	TBLDL	Program Memory Table Latch Low Byte									0000 0000	*****
23H	INTE0	GIE	ADCIE	TMBIE	TMAIE	LVD_BE	LVDE	E1IE	E0IE	000. 0000	*****	
24H	INTE1	I2CW7IE	I2CW6IE	I2CW5IE	I2CW4IE	I2CW3IE	I2CW2IE	I2CW1IE	I2CW0IE	000. 0000	*****	
25H	INTE2	-	-	-	-	-	I2CW10IE	I2CW9IE	I2CW8IE	000. 0000	*****	
26H	INTF0	-	ADCIF	TMBIF	TMAIF	LVD_BF	LVDF	E1IF	E0IF	000. 0000	w0	
27H	INTF1	I2CW7IF	I2CW6IF	I2CW5IF	I2CW4IF	I2CW3IF	I2CW2IF	I2CW1IF	I2CW0IF	000. 0000	w0	
28H	INTF2	-	-	-	-	-	I2CW10IF	I2CW9IF	I2CW8IF	000. 0000	w0	
29H	WREG	Working Register									xxxx xxxx	*****
2BH	STATUS	-	-	-	C	-	-	-	Z	...x xxxx*	
2CH	PSTATUS	BOR	PD	-	IDLE	ICP_Crst	STK_ERR	I2C_RST	I2C_GC_RST	000d .0..	rw0,rw0,rw0,rw0,-,rw0,-,-	
2DH	ADCR0H	ADC[19:12]									xxxx xxxx	*****
2EH	ADCR0M	ADC[11:4]									xxxx xxxx	*****
2FH	ADCR0L	ADC[3:0]				0	0	0	0		xxxx xxxx	*****
30H	ADCR1H	ADC[19]	ADC[19]	ADC[19]	ADC[19]	ADC[19]	ADC[18]	ADC[17]	ADC[16]	xxxx xxxx	*****	
31H	ADCR1M	ADC[15:8]									xxxx xxxx	*****
32H	ADCR1L	ADC[7:0]									xxxx xxxx	*****
33H	PWRCN0	ENBGR	ENTPS	ENSDR	INIS	TPSL	ENLDO	ENLVD	ENADC	000. 0000	*****	
34H	PWRCN1	ADHV	SDRV[1:0]		LVDV[1:0]		LDOV[1:0]			000. 0000	*****	
35H	ADCCN0	OSR[2:0]		VREGN		ADG[1:0]		SACM[1:0]			000. 0000	*****
36H	ADCCN1	INL[2:0]			INH[2:0]			VRI[1:0]			000. 0000	*****
37H	ADCCN2	DCSET[2:0]			RSNS[1:0]		-	-	ADRST	000. 0000	*****	
38H	CLKCN	-	-	-	HAOM[1:0]		CPUCKS	ENHAO	ENLPO	000. 0011	*****	
39H	AL_MO0	LSB for multiplexer input A / LSB for multiplexer output									xxxx xxxx	*****
3AH	AH_MO1	MSB for multiplexer input A / 15-8 bit multiplexer output									xxxx xxxx	*****
3BH	BL_MO2	LSB for multiplexer input B / 23-16 bit multiplexer output									xxxx xxxx	*****
3CH	BH_MO3	MSB for multiplexer input B / MSB for multiplexer output									xxxx xxxx	*****
3DH	PT0	-	-	PT0EG[1:0]		ENPWM10	PU0	TC0	PT0IO	000. 0000	*****	
3EH	PT1	-	-	PT1EG[1:0]		ENPWM00	PU1	TC1	PT1IO	000. 0000	*****	
3FH	PT2	-	-	-	-	ENPWM10	PU2	TC2	PT2IO	000. 0000	*****	
40H	PT3	-	-	-	-	ENPWM00	PU3	TC3	PT3IO	000. 0000	*****	

表 4-1 資料記憶體列表

“-”no use,“*”read/write,“w”write,“r”read,“r0”only read 0,“r1”only read 1,“w0”only write 0,“w1”only write 1
 “\$”for event status,“-”unimplemented bit,“x”unknown,“u”unchanged,“d”depends on condition

Address	File Name	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	A-RESET	R/W
41H	LSB_SEL	SEL_FLAG[7:0]								0000 0000	*****
42H	I2C_CMD	TIP	scu_L3	SP	0	0	0	0	EN_SCLO	0000 0000	RRRRRRRW
43H	I2C_O0	I2C Data Output Buffer 0								xxxx xxxx	w
44H	I2C_O1	I2C Data Output Buffer 1								xxxx xxxx	w
45H	I2C_O2	I2C Data Output Buffer 2								xxxx xxxx	w
46H	I2C_O3	I2C Data Output Buffer 3								xxxx xxxx	w
47H	I2C_O4	I2C Data Output Buffer 4								xxxx xxxx	w
48H	I2C_O5	I2C Data Output Buffer 5								xxxx xxxx	w
49H	I2C_O6	I2C Data Output Buffer 6								xxxx xxxx	w
4AH	I2C_O7	I2C Data Output Buffer 7								xxxx xxxx	w
4BH	I2C_I0	I2C Data Input Buffer 0								xxxx xxxx	r
4CH	I2C_I1	I2C Data Input Buffer 1								xxxx xxxx	r
4DH	I2C_I2	I2C Data Input Buffer 2								xxxx xxxx	r
4EH	I2C_I3	I2C Data Input Buffer 3								xxxx xxxx	r
4FH	I2C_I4	I2C Data Input Buffer 4								xxxx xxxx	r
50H	I2C_I5	I2C Data Input Buffer 5								xxxx xxxx	r
51H	I2C_I6	I2C Data Input Buffer 6								xxxx xxxx	r
52H	I2C_I7	I2C Data Input Buffer 7								xxxx xxxx	r
53H	I2C_I8	I2C Data Input Buffer 8								xxxx xxxx	r
54H	I2C_I9	I2C Data Input Buffer 9								xxxx xxxx	r
55H	I2C_I10	I2C Data Input Buffer 10								xxxx xxxx	r
56H	TMACN	ENTMA	TMACL	TMAS	DTMA[2:0]			-	-	0000 \$000	**** rw1,***
57H	TMAR	TMAR[7:0]								0000 0000	r,r,r,r,r,r,r,r
58H	TB1CN0	ENTMB	TB1M[1:0]		DTMB[1:0]		-	-	TMBCL	0000 0000	*****
59H	TB1C0L	TimerB1 counter Condition Register0 [7:0]								xxxx xxxx	*****
5AH	TB1C0H	TimerB1 counter Condition Register0 [15:8]								xxxx xxxx	*****
5BH	TB1C1L	TimerB1 counter Condition Register1 [7:0]								xxxx xxxx	*****
5CH	TB1C1H	TimerB1 counter Condition Register1 [15:8]								xxxx xxxx	*****
5EH	EE_CTRL	EN_TBL	PGM	0	0	0	0	0	0	0,1,1,1,1,1,0,0	
80H ~ FFH	GPR0	General Purpose Register as 128Byte								xxxx xxxx	

表 4-2 資料記憶體列表(續)

5. 電氣特性

5.1. Absolute Maximum Ratings

Absolute maximum ratings over operating free-air temperature (unless otherwise noted)

Voltage applied at VDD to VSS(VSSA)	-0.3 V to 6.5 V
Voltage applied at VDDA to VSS(VSSA)	-0.3 V to V _{DD} + 0.3 V
Voltage applied to any pin	-0.3 V to V _{DD} + 0.3 V
Storage temperature range, Tstg	-55°C to 125°C
Operating temperature range	-40°C to 85°C

5.2. Power System

Typical values are at TA = 25°C and VDD = 3.0V.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
V _{DD}	Supply Voltage		2.0		5.5	V
SDR	Temperature drift	VDD=VDDA=3.6V,		100		ppm/C
	Driving Current	VDD – Vs > 0.15			1000	uA
	Sensor Drive Voltage	SDRV[1:0]=00 SDRV[1:0]=01 SDRV[1:0]=10 SDRV[1:0]=11	1.50 2.05 2.65 3.42	1.65 2.20 2.80 3.80	1.80 2.35 2.95 4.18	V
RSENS	Internal Resistance for sensor	RSENS=00b, 0.0 Kohm RSENS =01b, 2.5 Kohm RSENS =01b, 5.0 Kohm RSENS =01b, 7.5 Kohm	2.25 4.5 6.75	0 2.5 5.0 7.5	2.75 5.5 8.25	Kohm
	Temperature drift	RSENS =01b, 2.5 Kohm			400	ppm/C
VDDA LDO	Current	VDDA = 1.65		12		uA
	Temperature drift	VDD=3.6V		100		ppm/C
	C load		100		10,000	nF
	R load			10K		KOhm
	VDDA LDO Voltage	LDOV[1:0]=01 LDOV[1:0]=10 LDOV[1:0]=11	2.15 2.75 3.65	2.30 2.90 3.80	2.45 3.05 3.95	V

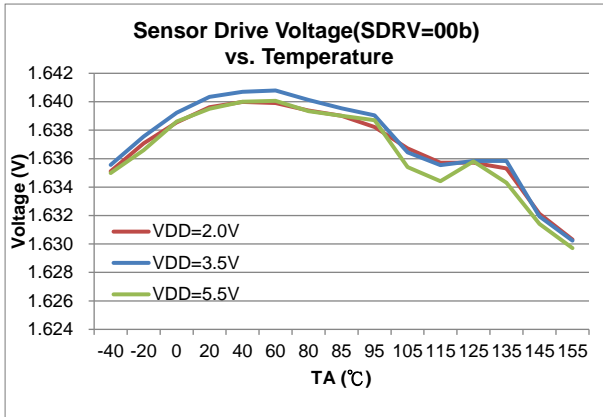


Figure 5.2-1(a) SDR vs. Temperature

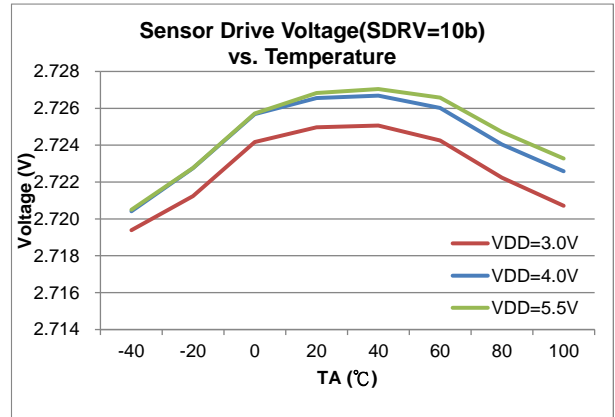


Figure 5.2-1(c) SDR vs. Temperature

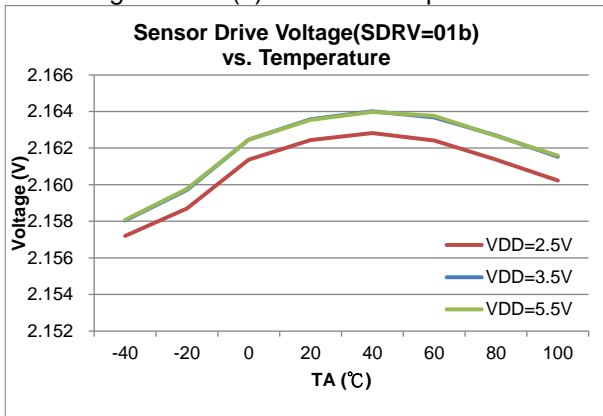


Figure 5.2-1(b) SDR vs. Temperature

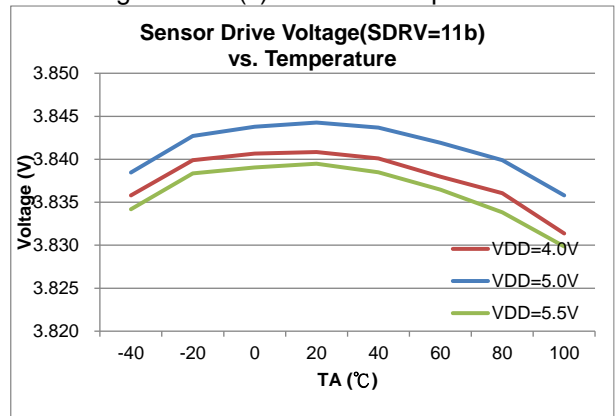


Figure 5.2-1(d) SDR vs. Temperature

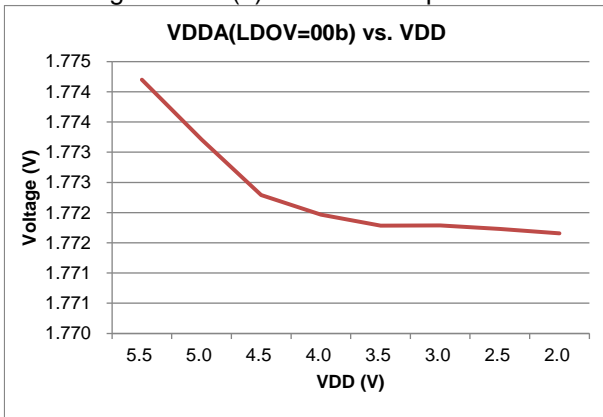


Figure 5.2-2(a) VDDA vs. VDD

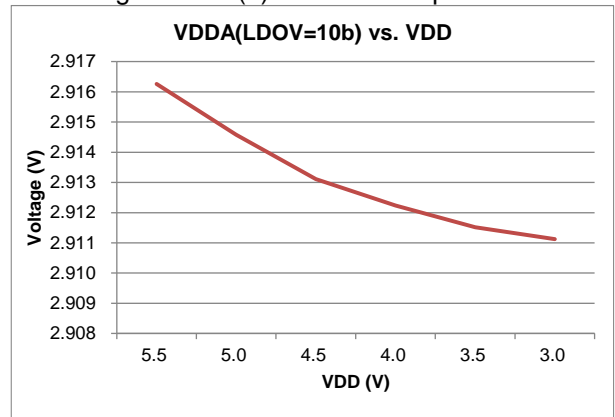


Figure 5.2-2(c) VDDA vs. VDD

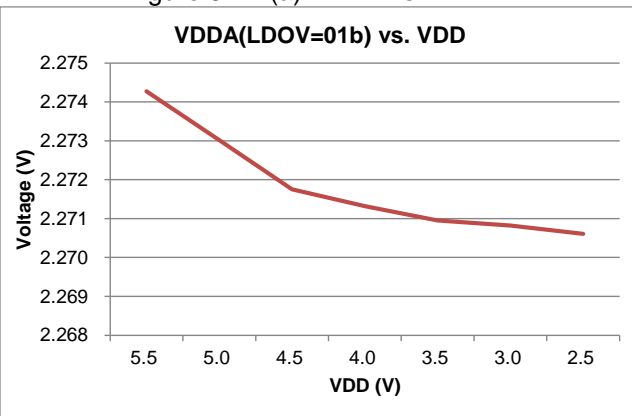


Figure 5.2-2(b) VDDA vs. VDD

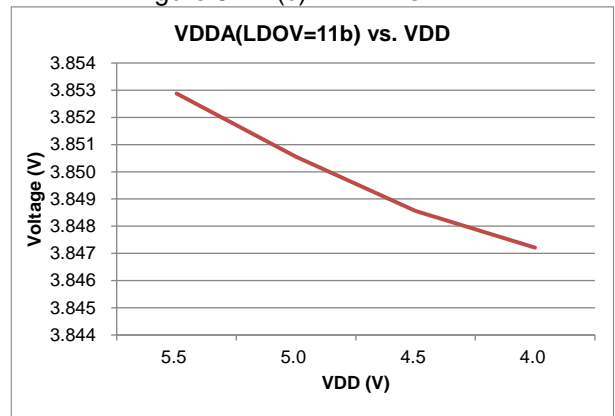


Figure 5.2-2(d) VDDA vs. VDD

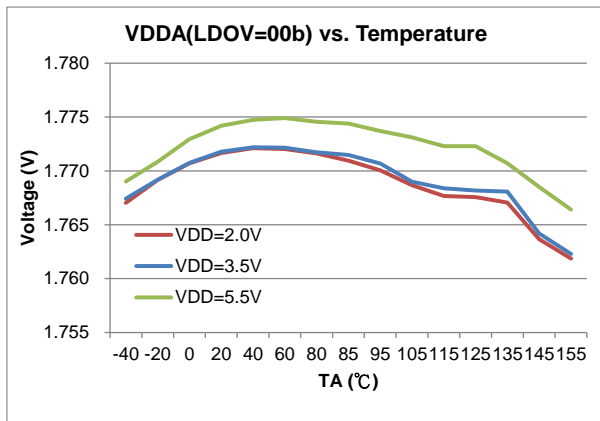


Figure 5.2-3(a) VDDA vs. Temperature

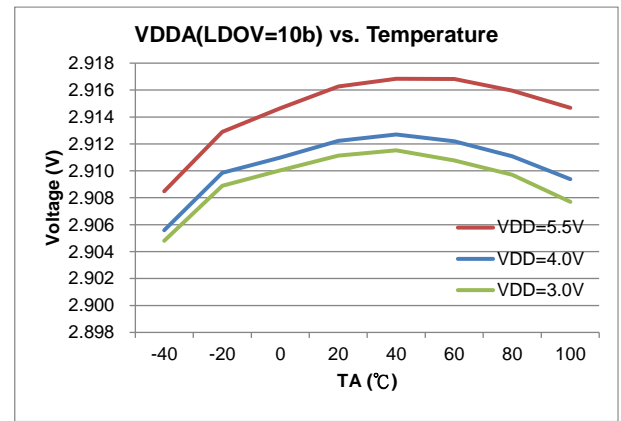


Figure 5.2-3(c) VDDA vs. Temperature

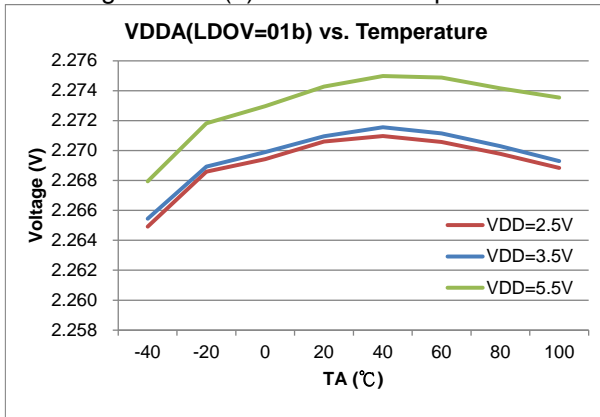


Figure 5.2-3(b) VDDA vs. Temperature

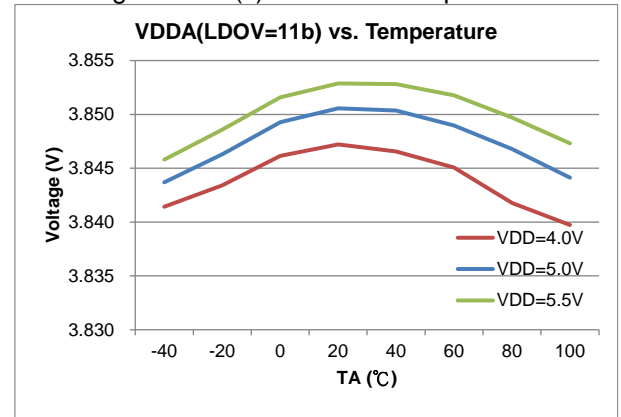


Figure 5.2-3(d) VDDA vs. Temperature

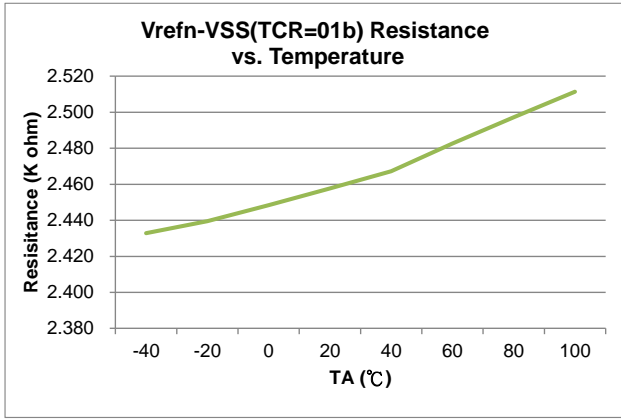


Figure 5.2-4(a) Vrefn resistance vs. Temperature

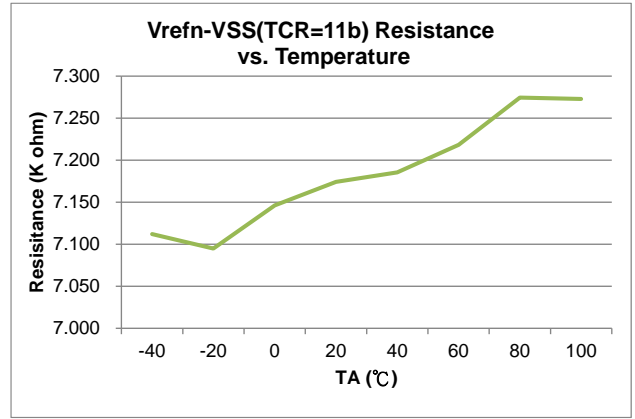


Figure 5.2-4(c) Vrefn resistance vs. Temperature

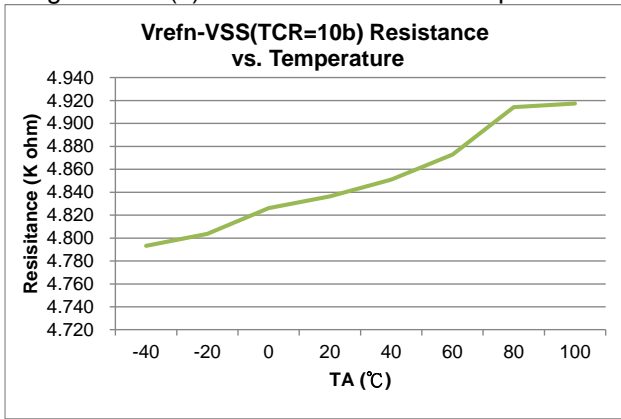


Figure 5.2-4(b) Vrefn resistance vs. Temperature

5.3. ΣΔADC, Power Supply and recommended operating conditions

Typical values are at TA = 25°C and VDD = 3.0V.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
	Input Range	Vr = Vrefp – Vrefn Gain = AD Gain x Ref Gain	- 0.8Vr/Gain		+ 0.8Vr/Gain	V
	Resolution	Total gain = 8		20		bit
	INL	OSR = 16384		±0.003	±0.01	%FSR
	Gain drift	VDD=VDDA=3.6V, OSR = 16384, Gain=8, ADC VR=external 2.048V/2. TA=-40°C~85°C		10		ppm/C
	Offset drift	VDD=VDDA=3.6V, OSR = 16384, Gain=8			1	%FSR
	Noise	Gain= 8 @ 8192 Gain=8 @ 128		1 15		uV
	Current		-		350	uA
	Offset		-	0.2	1	mV
	Sampling Rate		0.9	1	1.1	MS/s
	Input Gain		-	-	8	V/V
	ADC DC input shift	Vref = Vrefp – Vrefn		Vref/(4*gain)		V

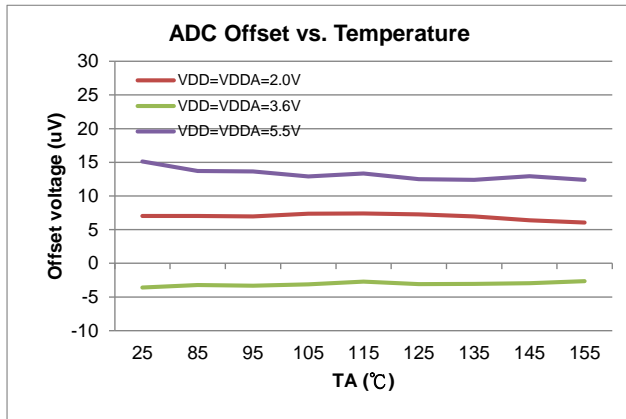


Figure 5.3-1 ADC Offset vs. Temperature

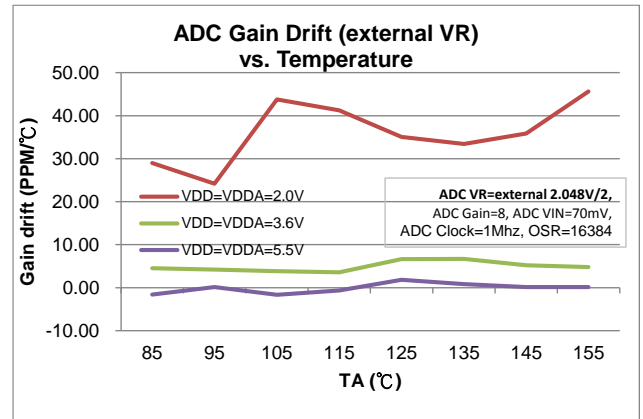
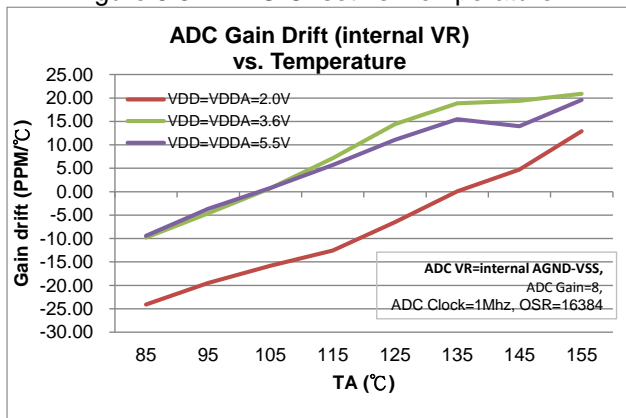


Figure 5.3-2 ADC Gain drift vs. Temperature
 Figure 5.3-3 ADC Gain drift vs. Temperature



5.4. Temperature sensor

Typical values are at TA = 25°C and VDD = 3.0V.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
	Resolution	After 2 points calculation; Monotonic	-	0.01	-	°C
	Temperature Sensor Slope		-	121	-	uV/°C
	Relative accuracy		+1	-	-1	uV/°C
KT	Absolute Temperature Scale 0°K					°C

5.5. Reset(Brownout, Low Voltage Detect)

Typical values are at TA = 25°C and VDD = 3.0V.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
LVD	Current	Including R	7.5			uA
	Temperature drift	TA=-40°C~85°C	100			ppm/C
	Low Voltage Detection	LVDV[1:0]=01 LVDV[1:0]=10 LVDV[1:0]=11	2.15 2.75 3.65	2.30 2.90 3.80	2.45 3.05 3.95	V
BOR	Detect Voltage		1.4	1.6	1.8	V
	Current		1 3			uA

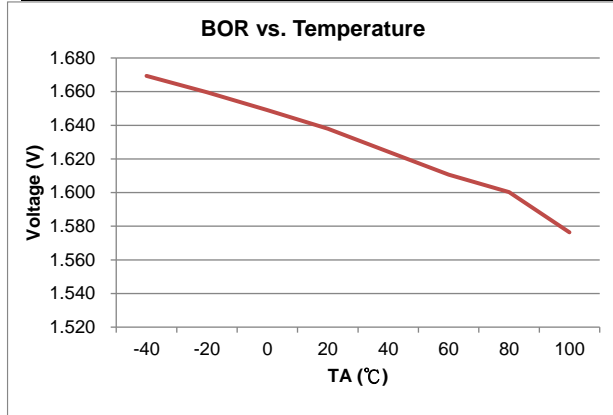


Figure 5.5-1 BOR vs. Temperature

5.6. Internal RC Oscillator

Typical values are at TA = 25°C and VDD = 3.0V.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
LPO	Low Power Oscillator frequency	VDD=2.0~5.5V, TA=-40°C~85°C	27.2	32	40.0	KHz
	Temperature drift	VDD=3.6V, TA=-40°C~85°C	50			ppm/C
	Current		1.5			uA
HAO	High Speed Oscillator frequency	VDD=2.0~5.5V, TA=-40°C~85°C	3.92	4	4.08	MHz
	Current		25			uA
	Temperature drift	VDD=3.6V, TA=-40°C~85°C	200			ppm/C

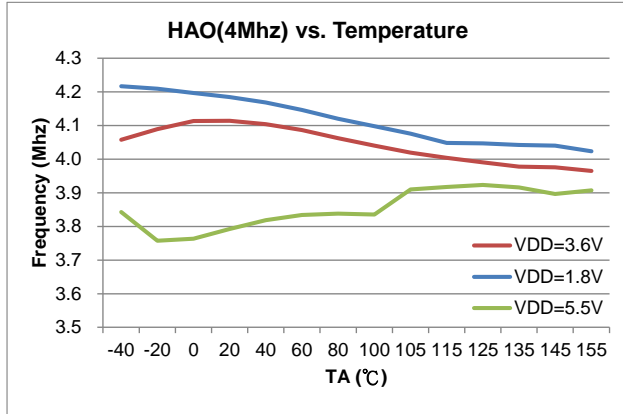


Figure 5.6-1 4Mhz HAO Frequency vs. Temperature

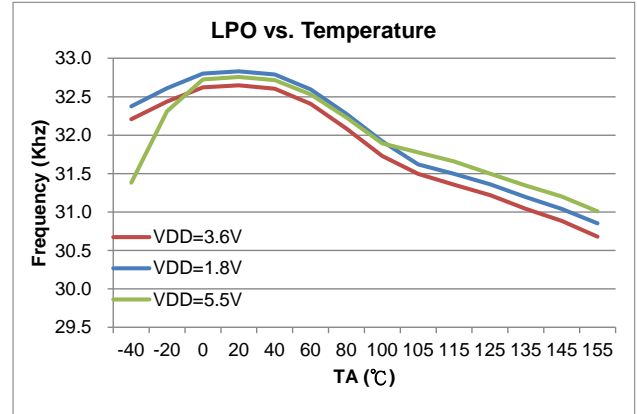


Figure 5.6-2 LPO Frequency vs. Temperature

5.7. Supply current

TA = 25°C, VDD = 3.6V, OSC_LPO = 32KHz, unless otherwise noted

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
IAM	Active mode	OSC_HAO = 4MHz, CPU_CK = 4MHz		800	1500	uA
ILP1	Low power mode 1	OSC_HAO = off, CPU_CK = LPO		6.5	13	uA
ILP2	Low power mode 2	OSC_HAO = off, CPU_CK = LPO, idle mode		1.65	5	uA
ILP3	Low power mode 3	OSC_HAO = off, CPU_CK = off, sleep mode		0.7	2	uA

TA = 25°C, VDD = 5.5V, OSC_LPO = 32KHz, unless otherwise noted.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
IAM	Active mode	OSC_HAO = 4MHz, CPU_CK = 4MHz		1100	2000	uA
ILP1	Low power mode 1	OSC_HAO = off, CPU_CK = LPO		11	25	uA
ILP2	Low power mode 2	OSC_HAO = off, CPU_CK = LPO, idle mode		2.5	6	uA
ILP3	Low power mode 3	OSC_HAO = off, CPU_CK = off, sleep mode		1	3	uA

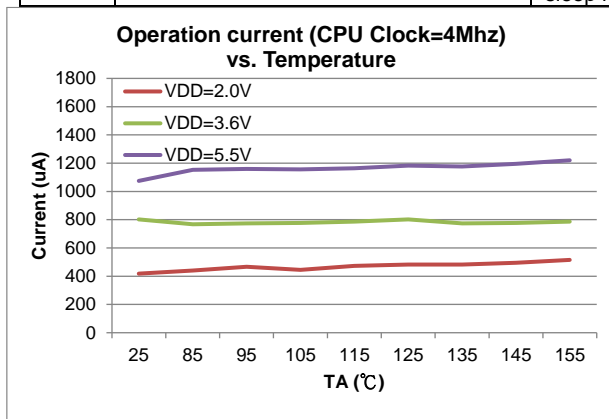


Figure 5.7-1 IAM3 vs. Temperature

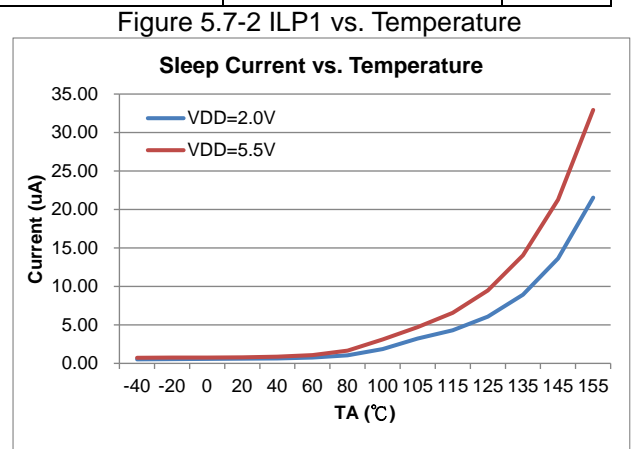


Figure 5.7-2 ILP1 vs. Temperature

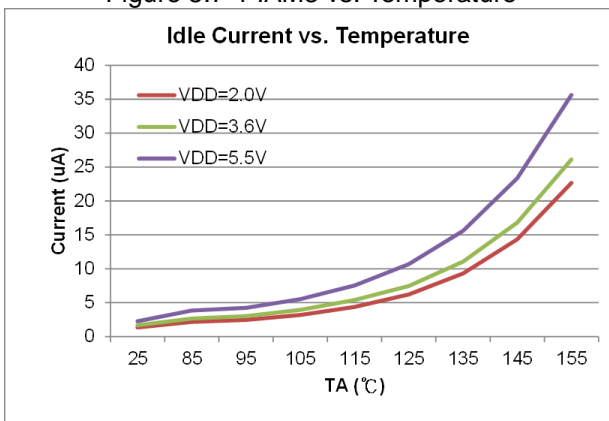


Figure 5.7-3 ILP2 vs. Temperature

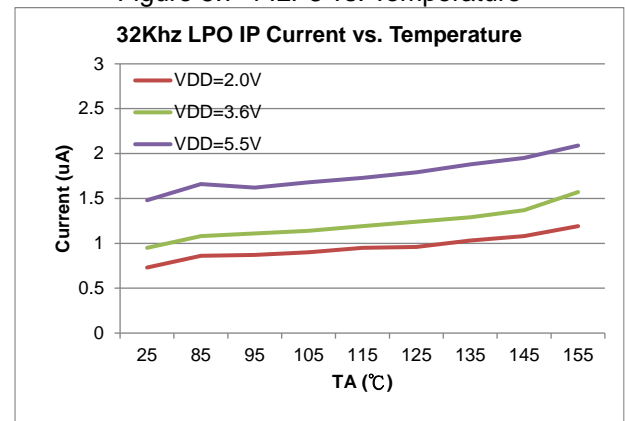
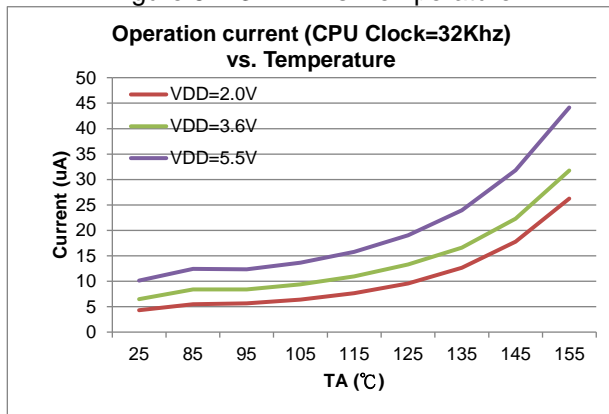


Figure 5.7-4 ILP3 vs. Temperature

Figure 5.7-5 LPO IP current vs. Temperature



5.8. Port

Typical values are at TA = 25°C and VDD = 3.0V.

Sym.	Parameter	Test Conditions	Min.	Typ.	Max.	unit
I ² C	I ² C interface speed				1	MHz
	SDA Output logic low (Open-drain)	IOL = 3mA	-	-	VDD X 0.2	V
	SDA, Output logic high	IOH = -50µA	VDD X 0.9	-	-	V
	SDA, SCL Input logic low		-	-	VDD X 0.2	V
	SDA, SCL Input logic high		VDD X 0.8	-	-	V
	SDA, SCL Digital input hysteresis		-	0.4	-	V
I/O	Sink	VDD = 3V, I/O= 0.3V	5			mA
	Source	VDD = 3V, I/O= 2.7V	5			mA
	Input H	VDD = 3V	1.6			V
	Input L	VDD = 3V			1.3	V

-

5.9. ΣΔADC Performance

HY14E10 針對 SD18 提供了重要的輸入雜訊規格。Table5.8-1 列出典型的雜訊規格表與 Gain, Output rate, 及單端最大輸入電壓等關係。測試條件設定在外部輸入訊號短路，參考電壓為(Vrefp-Vrefn)/2，取樣 1024 筆資料。

<i>HY14E10 ENOB(RMS) with OSR/GAIN at A/D Clock=1Mhz, VR=(Vrefp-Vrefn)/2</i>											
Max. Vin(mV) =0.9*VREF (1)	OSR			128	256	512	1024	2048	4096	8192	16384
	Output rate(HZ)			7813	3906	1953	977	488	244	122	61
	VDD	GAIN	SDR								
±157	3.3	8	2.8	14.3	15.9	16.3	16.4	16.4	17.1	17.3	18.7
<i>HY14E10 RMS Noise(uV) with OSR/GAIN at A/D Clock=1Mhz, VR=(Vrefp-Vrefn)/2</i>											
Max. Vin(mV) =0.9*VREF (1)	OSR			128	256	512	1024	2048	4096	8192	16384
	Output rate(HZ)			7813	3906	1953	977	488	244	122	61
	VDD	GAIN	SDR								
±157	3.3	8	2.8	16.8	5.7	4.2	4.1	4.1	2.4	2.1	0.8

Table5.8-1 SD18 ENOB and RMS Noise Table

The RMS noise are referred to the input. The Effective Number of Bits (ENOB(RMS Bit)) is defined as:

$$ENOB(RMS) = \frac{\ln\left(\frac{FSR}{RMS\ Noise}\right)}{\ln(2)}$$

$$RMS\ Noise = \frac{\left(2 \times VREF \times \sqrt{\sum_{k=1}^{1024} (ADO[k] - Average)^2}\right)}{2^{23}}$$

Where FSR (Full - Scale Range) = 2 × VREF/Gain.

$$Average = \frac{\sum_{k=1}^{1024} (ADO[k])}{1024}$$

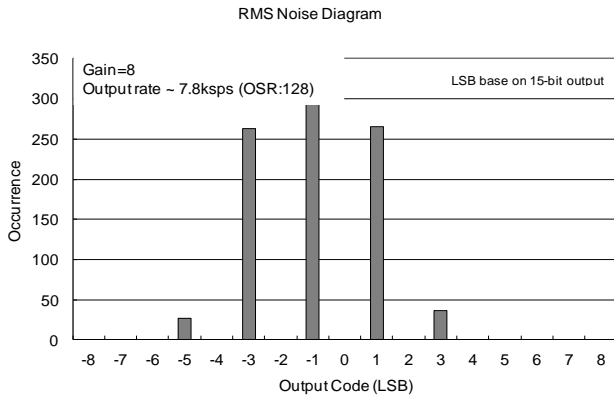


Figure5.9-1(a) RMS Noise Diagram

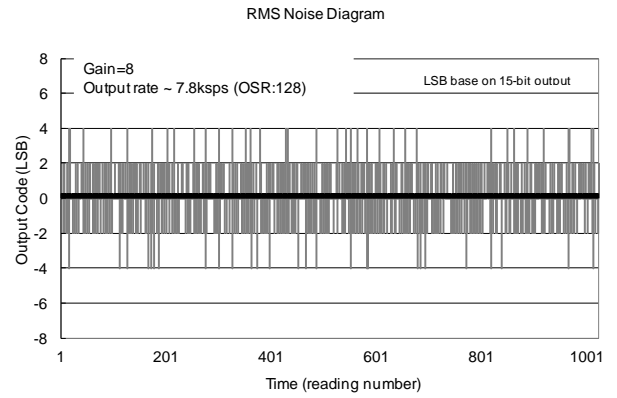


Figure5.9-1(b) Output Code Diagram

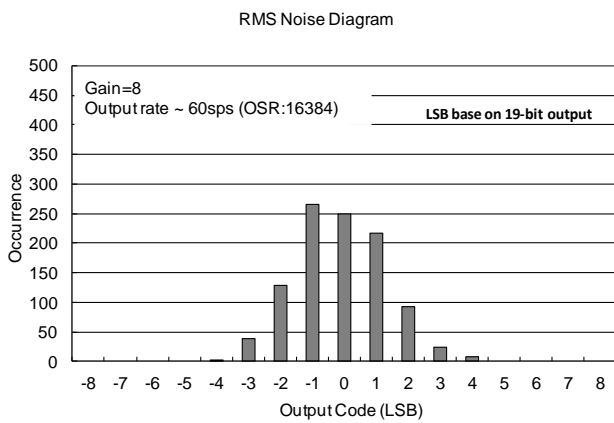


Figure5.9-2(a) RMS Noise Diagram

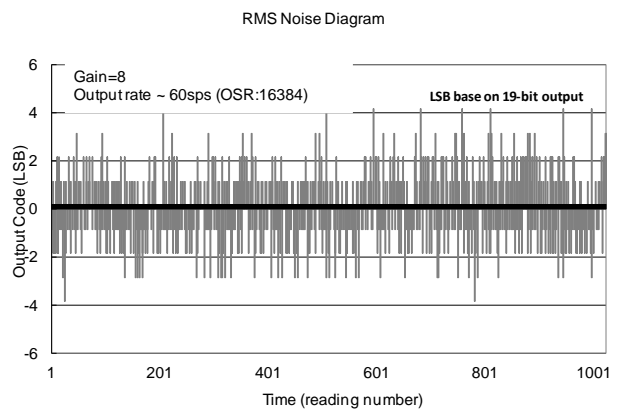


Figure5.9-2(b) Output Code Diagram

6. 訂貨資訊

下單品名 ^{1,5}	封裝型式	引腳數	封裝型式		程式碼 編號 ²	出貨包裝 形式	個裝 數量	材料 組成	MSL ³	操作溫度 範圍
			描述方式							
HY14E10-D000	Die	-	D	000	000	-	250	Green ⁴	-	-40°C~85°C
HY14E10-E016	SSOP	16	E	016	000	Tube	100	Green ⁴	MSL-3	-40°C~85°C
HY14E10-E016	SSOP	16	E	016	000	Tape & Reel	2500	Green ⁴	MSL-3	-40°C~85°C
HY14E10-N016	QFN	16	N	016	000	Tape & Reel	3000	Green ⁴	MSL-3	-40°C~85°C

¹ 產品名稱 – 封裝型式描述方式 – 程式碼編號 (空白片 / 標準品 / 代客燒錄碼)

例如：您的代客燒錄服務申請的程式碼編號為 007，且需要的產品是裸片出貨，對溫度要求為-40°C~ 85°C。則下單品名為 HY14E10-D000-007

例如：您的需求是不帶程式碼的空白片且需要的產品是裸片出貨，對溫度要求為-40°C~ 85°C。則下單品名為 HY14E10-D000

例如：您的需求是不帶程式碼的空白片且需要的產品是封裝片 QFN16 出貨，則下單品名為 HY14E10-N016，且需以 Tape & Reel 出貨，則除下單品名外，請特別註明出貨包裝形式為 Tape & Reel

例如：您的代客燒錄服務申請的程式碼編號為 008，而需求的產品是封裝片 SSOP 出貨，則下單品名為 HY14E10-E016-008，且需以 Tube 出貨，則除下單品名外，請特別註明出貨包裝形式為 Tube

² 程式碼編號

“001”~“999” 為標準品或代客燒錄申請的程式碼編號，而空白晶片不帶此碼。

³ MSL:

濕度敏感性等級係依據 IPC/JEDEC J-STD-020 的規範加以試驗分級，並參考 IPC/JEDEC J-STD-033 的標準處理、包裝、運輸與使用。

⁴ Green (RoHS & no Cl/Br):

HYCON 產品皆為 Green Product，符合 RoHS 指令，REACH 高關注物質(SVHC) 以及無鹵素相關規定。

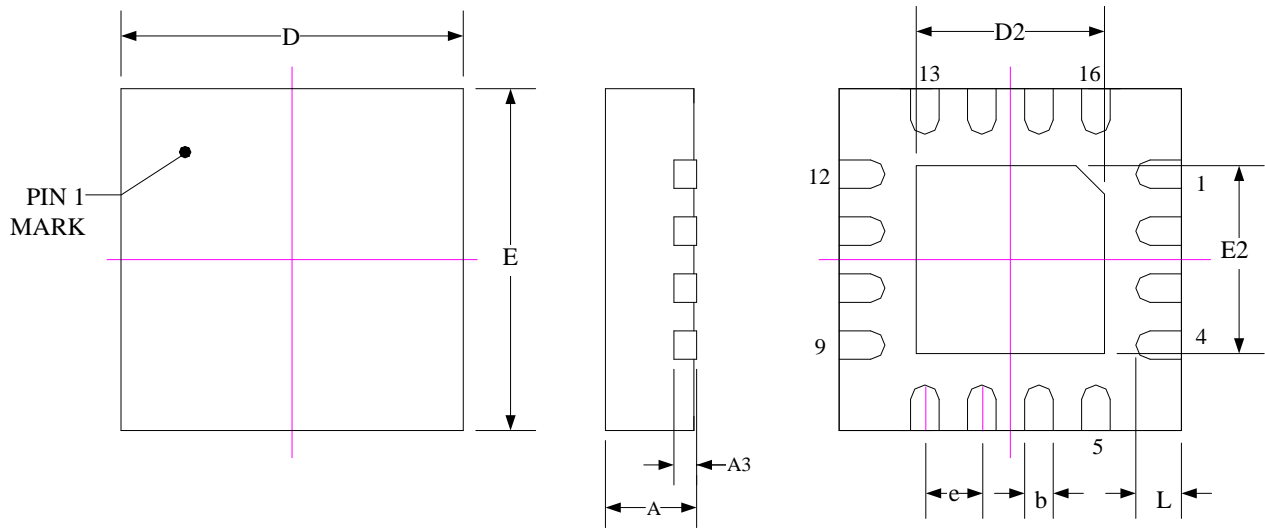
⁵ 下單品名:

HY14E10 表示晶片溫度操作範圍為-40°C~ 85°C。

7. 封裝型式資訊

7.1. QFN16(N016)

7.1.1. Package Outline Drawing QFN16(3x3x0.75)

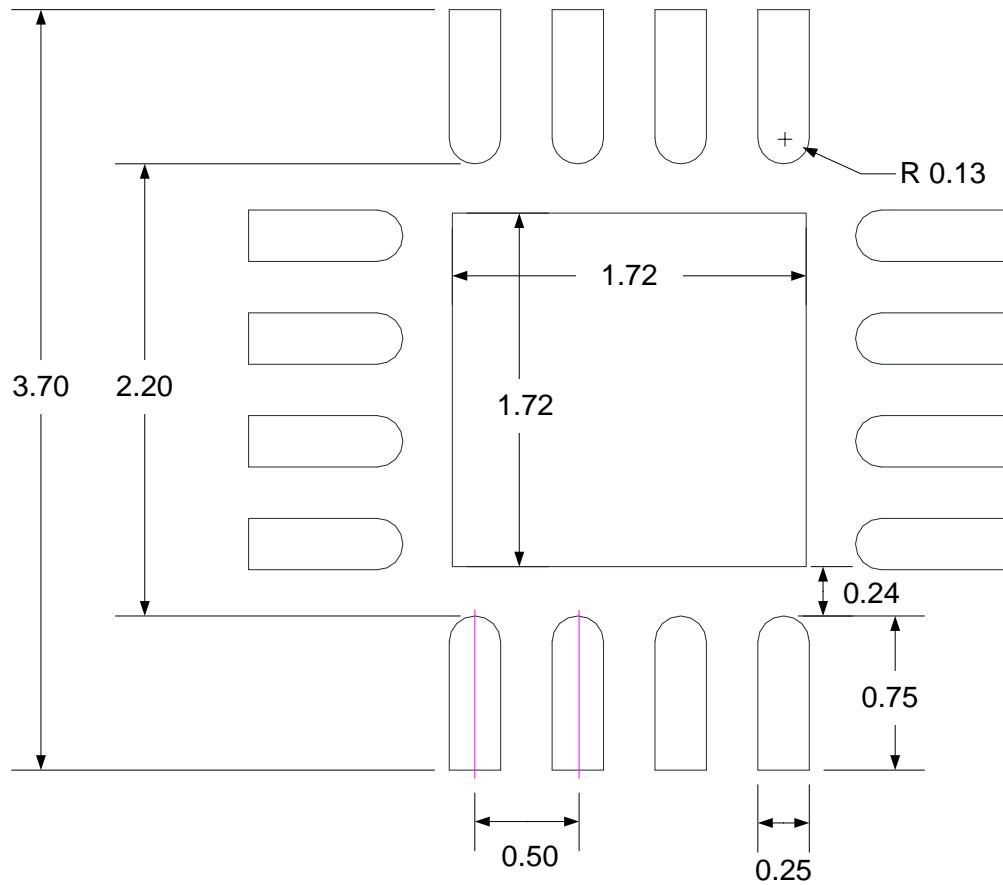


SYMBOLS	MIN	NOM	MAX
A	0.70	0.75	0.80
A3	0.203 REF.		
b	0.20	0.25	0.30
D	2.925	3.000	3.075
E	2.925	3.000	3.075
D2	1.625	1.725	1.825
E2	1.625	1.725	1.825
L	0.30	0.35	0.40
e	0.50 BASIC		

Note:

1. All dimensions refer to JEDEC OUTLINE MO-220.
2. Unit : mm
3. https://www.hycontek.com/hy_mcu/QFN_DFN_PCB.pdf

7.1.2. Land Pattern Design Recommendations QFN16(3x3x0.75)

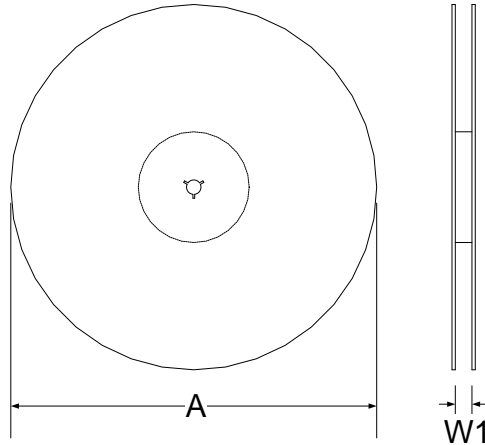


Note:

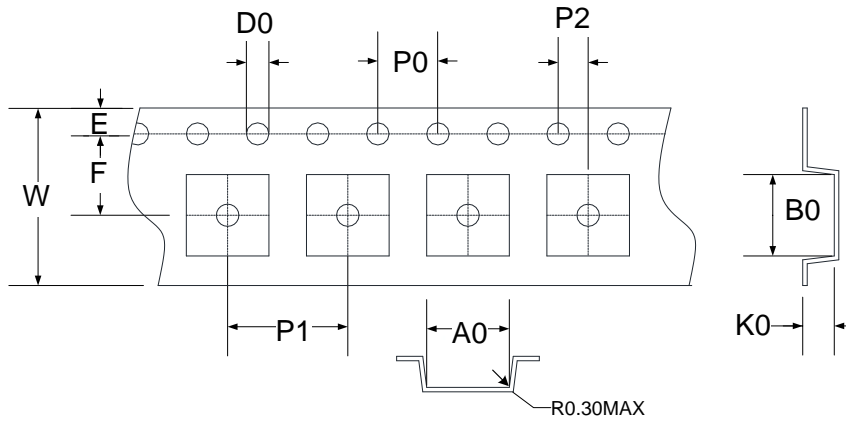
1. Publication IPC-7351 is recommended for alternate designs
2. Unit : mm
3. http://www.hycontek.com/wp-content/uploads/QFN_DFN_PCB.pdf

7.1.3. Tape & Reel Information QFN16(3x3x0.75)

1. Reel Dimensions



2. Carrier Tape Dimensions

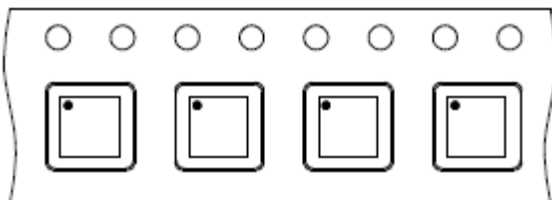


SYMBOLS	Reel Dimensions		Carrier Tape Dimensions									
	A	W1	A0	B0	K0	P0	P1	P2	E	F	D0	W
Spec.	330	12.5	3.30	3.30	1.10	4.00	8.00	2.00	1.75	5.50	1.50	12.00
Tolerance	+6/-3	+1.5/-0	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.10	±0.05	+0.1/-0	±0.30

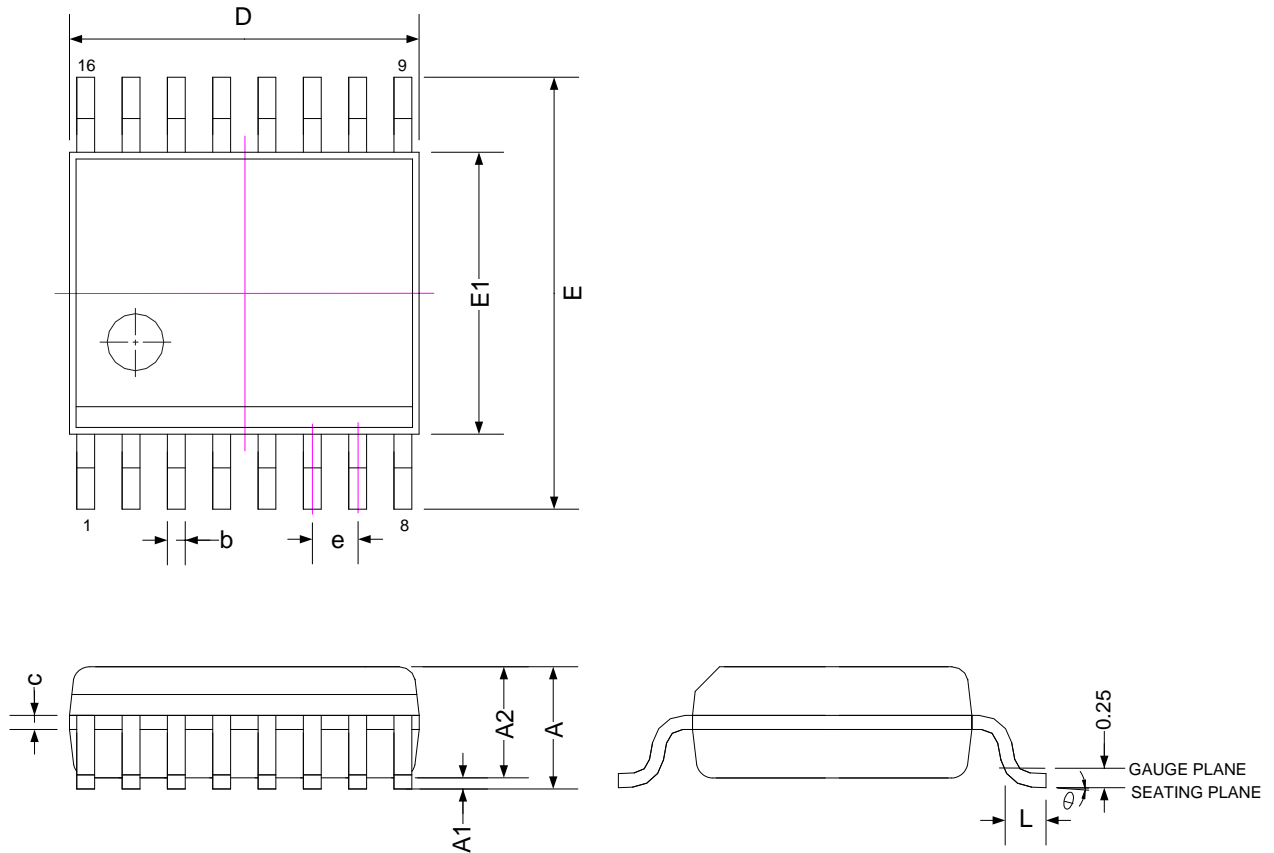
Note: 10 Sprocket hole pitch cumulative tolerance is ±0.20mm.

Unit: mm

3. Pin1 direction



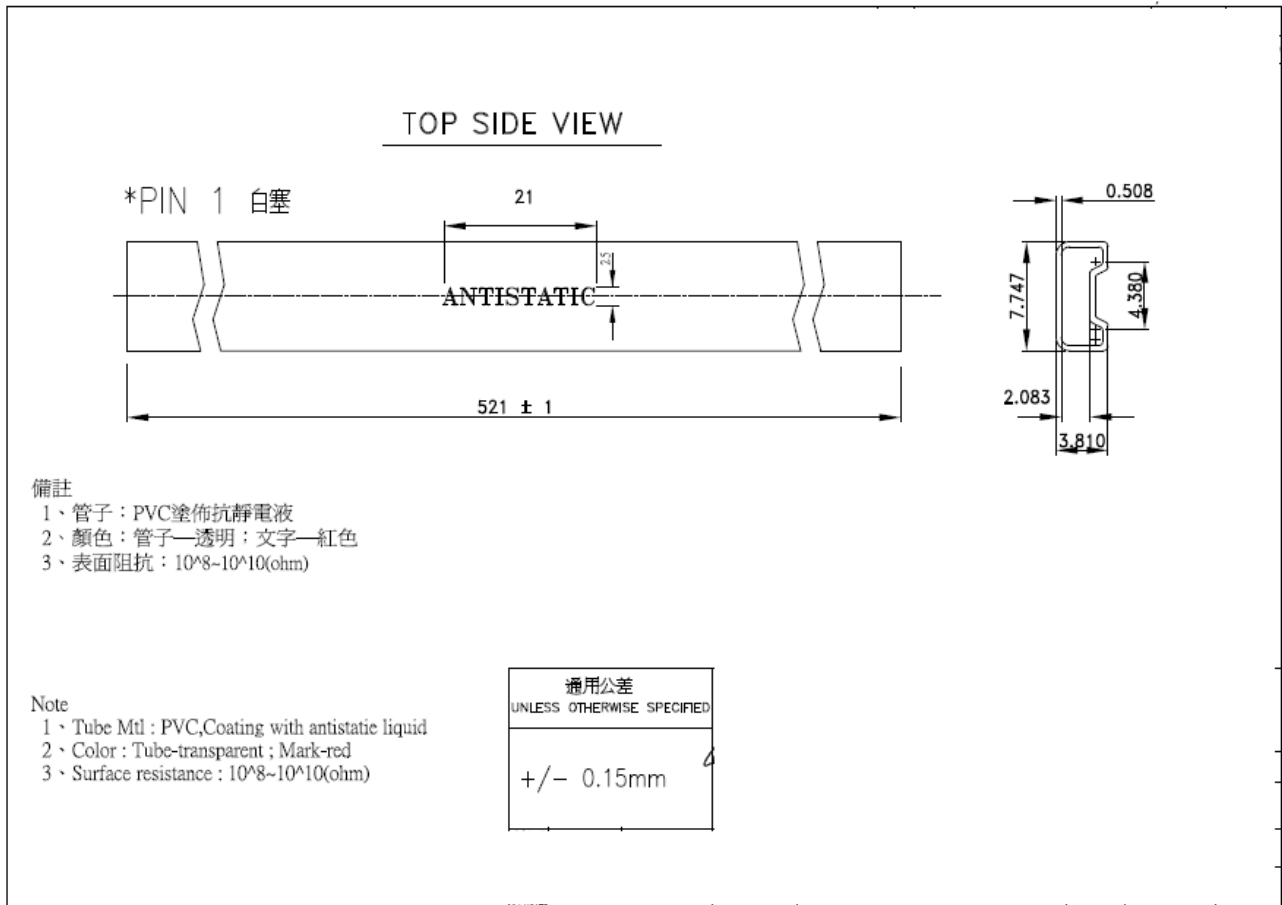
7.2. SSOP16(E016)
7.2.1. Package Outline Drawing SSOP16(150mil)



SYMBOLS	MIN	NOM	MAX
A	-	-	1.75
A1	0.10	0.15	0.25
A2	-	-	1.50
b	0.20	-	0.30
c	0.18	-	0.25
D	4.80	4.90	5.00
E1	3.81	3.91	3.99
E	5.79	5.99	6.20
L	0.41	-	1.27
e	0.635 BASIC		
θ°	0	-	8

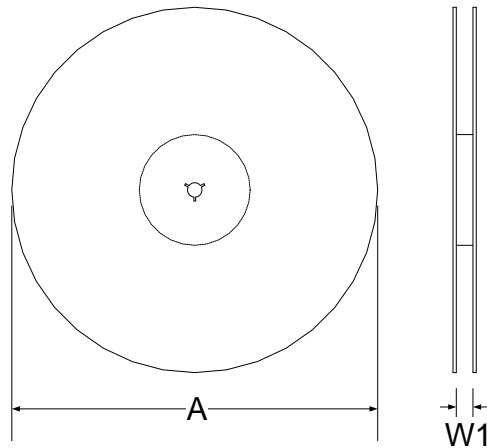
- Note:
1. All dimensions refer to JEDEC OUTLINE MO-137.
 2. Do not include Mold Flash or Protrusions.
 3. Unit: mm

7.2.2. Tube Dimensions SSOP16(150mil)

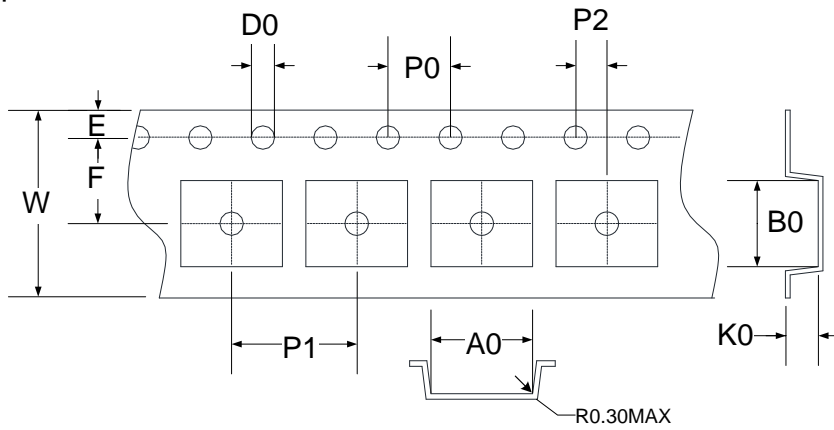


7.2.3. Tape & Reel Information SSOP16(150mil)-Type 1

1. Reel Dimensions



2. Carrier Tape Dimensions

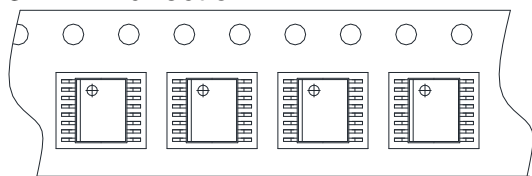


SYMBOLS	Reel Dimensions		Carrier Tape Dimensions									
	A	W1	A0	B0	K0	P0	P1	P2	E	F	D0	W
Spec.	330	12.5	6.90	5.40	2.00	4.00	8.00	2.00	1.75	5.50	1.50	12.00
Tolerance	+6/-3	+1.5/-0	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.10	±0.05	+0.1/-0	±0.30

Note: 10 Sprocket hole pitch cumulative tolerance is ±0.20mm.

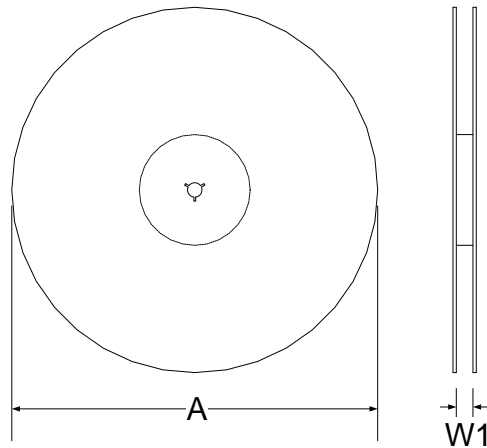
Unit: mm

3. Pin1 direction

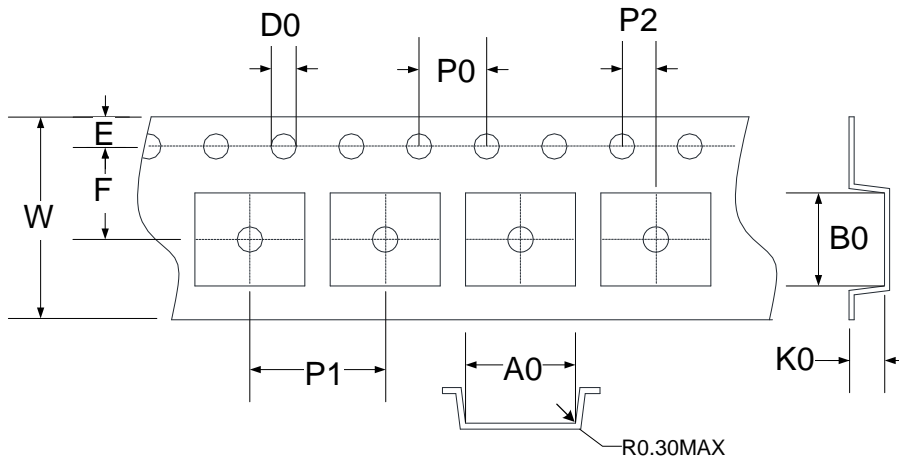


7.2.4. Tape & Reel Information SSOP16(150mil) -Type 2

1. Reel Dimensions



2. Carrier Tape Dimensions

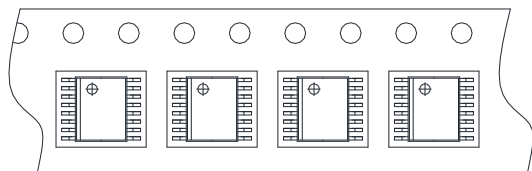


SYMBOLS	Reel Dimensions		Carrier Tape Dimensions									
	A	W1	A0	B0	K0	P0	P1	P2	E	F	D0	W
Spec.	330	12.5	6.50	5.20	2.10	4.00	8.00	2.00	1.75	5.50	1.50	12.00
Tolerance	+6/-3	+1.5/-0	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.10	±0.05	+0.1/-0	±0.30

Note: 10 Sprocket hole pitch cumulative tolerance is ±0.20mm.

Unit: mm

3. Pin1 direction



8. 修訂記錄

以下描述本檔差異較大的地方，而標點符號與字形的改變不在此描述範圍。

版次	頁次	摘要
V01	All	初版發行
V02	12-13	修改 VDDA 輸出電壓、ADC Performance
V03	All	增加 QFN16, SSOP16 封裝引腳
V04	6	更正內部方塊圖為 111bytes EEPROM 區塊可供使用者使用
	8	修正 SD18 Network 方塊圖描述在 TPSH 和 TPSL
	27	新增相關封裝形式資訊
V05	All	新增說明，在電壓放大倍率 x1/x2/x4 為 Reserved，建議使用 8 倍放大倍率。
	All	新增 HY14E10 ENOB and RMS Table 和 RMS Noise Diagram
V06	All	新增溫度曲線圖與-40C~125C 規格內容
V07	All	刪除 TSSOP28 封裝引腳
	All	刪除 HY14E10M 產品規格
	20	修正 BOR 偵測電壓範圍由原本的 1.5V~1.71V 改至 1.4V~1.8V
V08	All	刪除 2MHz 及 8MHz 的 HAO 規格
	5	新增功能列表
	14	修正 5.2 章節中的 SDR 及 VDDA LDO 規格
	20	修正 5.5 章節中的 LVD 規格
	21	修正 5.6 章節中的 LPO 及 4MHz HAO 規格
V09	7	標示 VDD 建議電容大小
	15	增加 RSENS 規格
	23	增加 VDD=5V 時 Supply current 規格
	23	增加 VDD=3.6V 時 Supply current MAX 規格
V10	26	更新 QFN16 產品的 Tape & Reel 包裝之個裝數量